

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Richard L. Hilton et al.

Examiner: Son T. Dinh

Serial No.: 10/765,484

Group Art Unit: 2824

Filed: January 27, 2004

Docket No.: 200316177-1

Title: **MEMORY CELL STRINGS****COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE**

Mail Stop: Issue Fee  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Please enter the following Response to Examiner's Reasons for Allowance.  
Remarks begin on page 2.

**AUTHORIZATION TO DEBIT ACCOUNT**

It is believed that no extensions of time or fees for net addition of claims are required, beyond those, which may otherwise be provided for in documents accompanying this paper. However, in the event that additional extensions of time are necessary to allow consideration of this paper, such extensions are hereby petitioned under 37 C.F.R. § 1.136(a), and any fees required therefore (including fees for net addition of claims) are hereby authorized to be charged to Hewlett-Packard Development Company's deposit account no. 08-2025.



## REMARKS

The Examiner provides the following reasons for allowance:

[t]he prior art of record fail (sic) to teach or suggest a method of performing a read operation in a MRAM comprising the steps of applying a first constant current (of first constant voltage) through a memory cell string, measuring (a first voltage (or first current) across the memory cell string, applying a second current across the MRAM, the second current is a write sense current, measuring a second voltage (or third current) across the memory cell string and determining whether the first voltage (or first current) differs from the second voltage (or third current) as claimed in claims 1 and 12; a memory cell string comprising a first memory cell and a second memory cell connected in series, a current source for applying a first current through the string, a circuit coupled to the memory cell string for detecting a change in a voltage across the memory cell string in response to the current source applying the constant current through the memory cell string and a second current being adapted across the first memory cell, the second current comprising a write sense current (claims 7 and 18).

Applicant agrees that the claims are allowable for at least these reasons. However, the claims are allowable for other reasons as well. Applicant submits that the present claims are allowable for at least the reason that the references of record in the application do not teach or suggest all the limitations of the claims as recited in the claims themselves. To the extent that the Examiner's reasons for allowance may suggest the claims contain any features that are not specifically recited, Applicant respectfully disagrees with this characterization of the claims.

Date: April 12, 2005

Respectfully submitted,



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